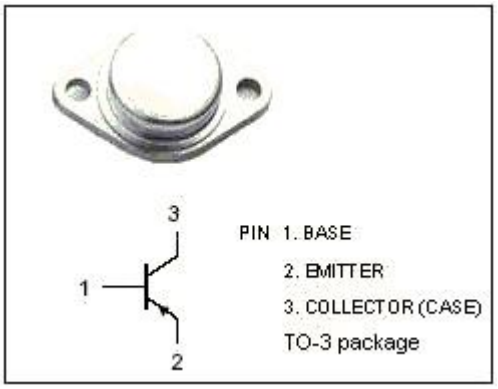
isc Silicon PNP Power Transistor 2SA980

DESCRIPTION

- High Power Dissipation-
  : P_C= 80W(Max.)@T_C=25℃
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -100V(Min.)
- Complement to Type 2SC2260
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

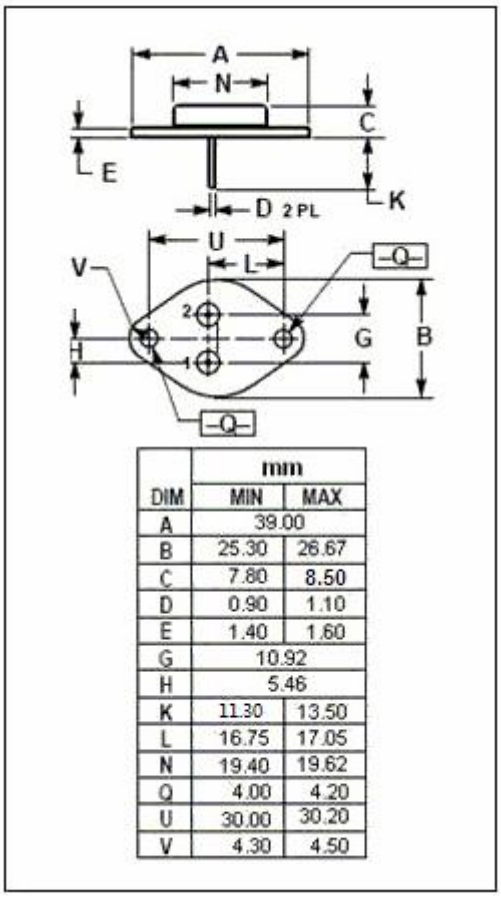


APPLICATIONS

- Designed for general purpose applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-8	A
I_B	Base Current-Continuous	-3	A
P_C	Collector Power Dissipation @T_C=25℃	80	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65~150	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -50mA; I_B= 0	-100			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -3A; I_B= -0.3A			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -100V; I_E= 0			-0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -6V; I_C= 0			-0.1	mA
h_{FE}	DC Current Gain	I_C= -3A; V_{CE}= -4V	30			
f_T	Current-Gain—Bandwidth Product	I_E= 0.5A; V_{CE}= -12V		20		MHz
Switching times						
t_r	Rise Time	I_C= -3A ,R_L= 4Ω , V_{CC}= -12V I_{B1}= -0.2A; I_{B2}= 0.1A		0.85		μs
t_{stg}	Storage Time			2.0		μs
t_f	Fall Time			0.3		μs